

isc Silicon NPN Power Transistor

2SC3850

DESCRIPTION

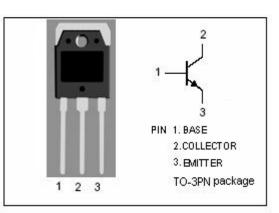
- High Collector-Emitter Sustaining Voltage-: V_{CEO(SUS)}= 400V(Min)
- · Good Linearity of hFE
- High Collector Current
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

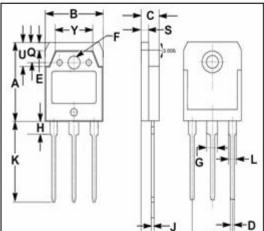
APPLICATIONS

• Designed for power switching and general purpose applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)					
SYMBOL	PARAMETER	VALUE	UNIT		
V _{CBO}	Collector-Base Voltage	500	V		
Vces	Collector-Emitter Voltage	500	V		
V _{CEO}	Collector-Emitter Voltage	400	V		
V _{EBO}	Emitter-Base voltage	7	V		
lc	Collector Current-Continuous	20	A		
I _{CM}	Collector Current-Peak	30	A		
Ів	Base Current-Continuous	6	А		
Pc	Collector Power Dissipation @ T_c =25°C	125	W		
	Collector Power Dissipation @ $T_a=25^{\circ}C$	2.5			
TJ	Junction Temperature	150	°C		
T _{stg} Storage Temperature Range		-55~150	°C		

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)





	mm		
DIM	MIN	MAX	
Α	19.60	20.10	
В	15.50	15.70	
С	4.70	4.90	
D	0.90	1.10	
E	1.90	2.10	
F	3.40	3.60	
G	2.90	3.20	
Н	3.20	3.40	
J	0.595	0.605	
Κ	20.00	20.70	
L	1.90	2.20	
N	10.89	10.91	
Q	4.90	5.10	
R	3.35	3.45	
S	1.995	2.100	
U	5.90	6.10	
Y	9.90	10.10	

isc website: www.iscsemi.com



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ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 30mA; I _B =0	400			V
$V_{\text{CE}(\text{sat})}$	Collector-Emitter Saturation Voltage	I _C = 10A; I _B = 2A			1.0	V
$V_{\text{BE}(\text{sat})}$	Base-Emitter Saturation Voltage	I _C = 10A; I _B = 2A			1.5	V
I _{СВО}	Collector Cutoff Current	V _{CB} = 500V ; I _E = 0			100	μA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 7V; I _C = 0			100	μA
h _{FE-1}	DC Current Gain	I _C = 2A ; V _{CE} = 5V	15			
h _{FE-2}	DC Current Gain	I _C = 10A ; V _{CE} = 5V	10			
f⊤	Current-Gain—Bandwidth Product	I _C = 1A ; V _{CE} = 10V; f= 1MHz		15		MHz

Switching Times

t _{on}	Turn-on Time			1.0	μ S
t _{stg}	Storage Time	I _C = 10A, I _{B1} = -I _{B2} = 2A; V _{CC} = 125V		2.5	μ s
t _f	Fall Time			1.0	μ S

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